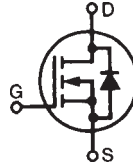


# X3-Class Power MOSFET™

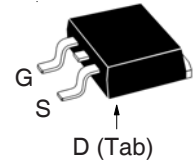
## IXTA90N20X3

$$\begin{aligned} V_{DSS} &= 200V \\ I_{D25} &= 90A \\ R_{DS(on)} &\leq 12m\Omega \end{aligned}$$

N-Channel Enhancement Mode  
Avalanche Rated



TO-263



G = Gate      D = Drain  
S = Source    Tab = Drain

Symbol	Test Conditions	Maximum Ratings	
$V_{DSS}$	$T_J = 25^\circ\text{C}$ to $175^\circ\text{C}$	200	V
$V_{DGR}$	$T_J = 25^\circ\text{C}$ to $175^\circ\text{C}$ , $R_{GS} = 1M\Omega$	200	V
$V_{GSS}$	Continuous	$\pm 20$	V
$V_{GSM}$	Transient	$\pm 30$	V
$I_{D25}$	$T_C = 25^\circ\text{C}$	90	A
$I_{DM}$	$T_C = 25^\circ\text{C}$ , Pulse Width Limited by $T_{JM}$	220	A
$I_A$	$T_C = 25^\circ\text{C}$	45	A
$E_{AS}$	$T_C = 25^\circ\text{C}$	1	J
$dv/dt$	$I_S \leq I_{DM}$ , $V_{DD} \leq V_{DSS}$ , $T_J \leq 150^\circ\text{C}$	20	V/ns
$P_D$	$T_C = 25^\circ\text{C}$	390	W
$T_J$		-55 ... +175	$^\circ\text{C}$
$T_{JM}$		175	$^\circ\text{C}$
$T_{stg}$		-55 ... +175	$^\circ\text{C}$
$T_L$	Maximum Lead Temperature for Soldering	300	$^\circ\text{C}$
$dT/dt$	Heating / Cooling rate, $175^\circ\text{C} - 210^\circ\text{C}$	50	$^\circ\text{C}/\text{min}$
$T_{SOLD}$	1.6 mm (0.062in.) from Case for 10s	260	$^\circ\text{C}$
$F_C$	Mounting Force	10..65 / 2.2..14.6	N/lb
Weight		2.5	g

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$BV_{DSS}$	$V_{GS} = 0V$ , $I_D = 250\mu A$	200		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 250\mu A$	2.5		4.5 V
$I_{GSS}$	$V_{GS} = \pm 20V$ , $V_{DS} = 0V$			$\pm 100$ nA
$I_{DSS}$	$V_{DS} = V_{DSS}$ , $V_{GS} = 0V$ $T_J = 125^\circ\text{C}$			5 $\mu A$ 100 $\mu A$
$R_{DS(on)}$	$V_{GS} = 10V$ , $I_D = 0.5 \cdot I_{D25}$ , Note 1			12 m $\Omega$

### Features

- International Standard Package
- Low  $R_{DS(ON)}$  and  $Q_G$
- Avalanche Rated
- Low Package Inductance

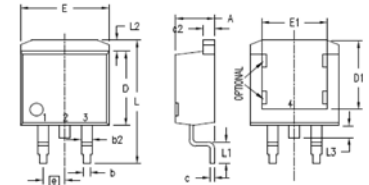
### Advantages

- High Power Density
- Easy to Mount
- Space Savings

### Applications

- Switch-Mode and Resonant-Mode Power Supplies
- DC-DC Converters
- PFC Circuits
- AC and DC Motor Drives
- Robotics and Servo Controls

Symbol		Test Conditions		Characteristic Values		
(T <sub>J</sub> = 25°C, Unless Otherwise Specified)		Min.	Typ.	Max		
g <sub>fs</sub>	V <sub>DS</sub> = 10V, I <sub>D</sub> = 0.5 • I <sub>D25</sub> , Note 1	60	100			S
R <sub>Gi</sub>	Gate Input Resistance		1.4			Ω
C <sub>iss</sub>	V <sub>GS</sub> = 0V, V <sub>DS</sub> = 25V, f = 1MHz		5420			pF
C <sub>oss</sub>			930			pF
C <sub>rss</sub>			4			pF
Effective Output Capacitance						
C <sub>o(er)</sub>	Energy related	V <sub>GS</sub> = 0V V <sub>DS</sub> = 0.8 • V <sub>DSS</sub>	420			pF
C <sub>o(tr)</sub>	Time related		1300			pF
t <sub>d(on)</sub>	Resistive Switching Times	V <sub>GS</sub> = 10V, V <sub>DS</sub> = 0.5 • V <sub>DSS</sub> , I <sub>D</sub> = 0.5 • I <sub>D25</sub> R <sub>G</sub> = 5Ω (External)	22			ns
t <sub>r</sub>			26			ns
t <sub>d(off)</sub>			62			ns
t <sub>f</sub>			13			ns
Q <sub>g(on)</sub>	V <sub>GS</sub> = 10V, V <sub>DS</sub> = 0.5 • V <sub>DSS</sub> , I <sub>D</sub> = 0.5 • I <sub>D25</sub>		78			nC
Q <sub>gs</sub>			23			nC
Q <sub>gd</sub>			22			nC
R <sub>thJC</sub>						0.32 °C/W

**TO-263 (IXTA) Outline**


- 1 = Gate  
2 = Drain  
3 = Source  
4 = Drain

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.160	.190	4.06	4.83
A1	.080	.110	2.03	2.79
b	.020	.039	0.51	0.99
b2	.045	.055	1.14	1.40
c	.016	.029	0.40	0.74
c2	.045	.055	1.14	1.40
D	.340	.380	8.64	9.65
D1	.315	.350	8.00	8.89
E	.380	.410	9.65	10.41
E1	.245	.320	6.22	8.13
e	.100 BSC		2.54 BSC	
L	.575	.625	14.61	15.88
L1	.090	.110	2.29	2.79
L2	.040	.055	1.02	1.40
L3	.050	.070	1.27	1.78
L4	0	.005	0	0.13

**Source-Drain Diode**

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max
$I_S$	$V_{GS} = 0\text{V}$			90 A
$I_{SM}$	Repetitive, pulse Width Limited by $T_{JM}$			360 A
$V_{SD}$	$I_F = I_S$ , $V_{GS} = 0\text{V}$ , Note 1			1.4 V
$t_{rr}$	$I_F = 45\text{A}$ , $-di/dt = 100\text{A}/\mu\text{s}$ $V_R = 100\text{V}$		124	ns
$Q_{RM}$			650	nC
$I_{RM}$			10.5	A

Note 1. Pulse test,  $t \leq 300\mu\text{s}$ , duty cycle,  $d \leq 2\%$ .

**ADVANCE TECHNICAL INFORMATION**

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065B1	6,683,344	6,727,585	7,005,734B2	7,157,338B2
	4,860,072	5,017,508	5,063,307	5,381,025	6,259,123B1	6,534,343	6,710,405B2	6,759,692	7,063,975B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728B1	6,583,505	6,710,463	6,771,478B2	7,071,537	

IXYS REF: T\_90N20X3(25-S202) 5-31-17-A



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